MBR1560P5Q

Schottky Diodes

ð High f ency ope ð High p V y , high tempe Me ep xy enc] enhanced mechanical strengand m _ istrV p ance
ð Guard ring for enhanced ruggedness and long term reliability
ð Part no . with suffix Q means AEC - Q101 qualified

Typical Applications

Typical applications are in switching power supplies, converters, automotive, freewheeling diodes, and reverse battery protection.

Mechanical Data = l' ' 2 d l A mw Ď }

ðTerminals: Tin plated leads, solderable per J-STD-002 and JESD22-B102
- **Polarity**: As marked

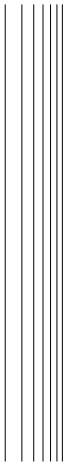
■Maximum Ratings (T_a=25 Unless otherwise specified

PARAMETER	SYMBOL		
Repetitive peak reverse voltage	V_{RRM}	V	60
Average Rectified Output Current @60Hz - sine wave $_c$=105	I_O	A	15
Forward Surge Current (Non-repetitive) @60Hz half-sine wave,1 cycle, T_a=25	I_{FSM}	A	200
Current Squared Time @1ms≤t≤8.3ms T_J=25	I^2t	A^2s	166
Storage Temperature	T_{stg}		-55 ~ +150
Junction Temperature	T_J		-55 ~ +150

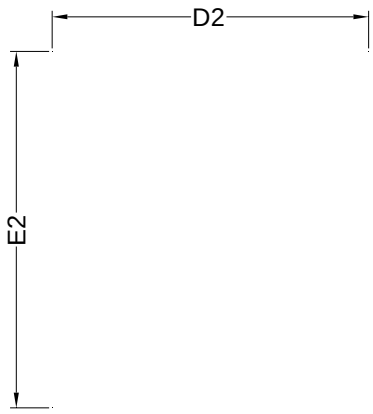
■Electrical Characteristics T_a=25 Unless otherwise specified

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS		Typ	Max
Instantaneous forward voltage	V_F	V	I_F=15A	T_J=25	0.68	0.8
			I_F=15A	T_J=125	0.59	0.7
Typical junction capacitance	C_J	pF	V_R=4V, f=1 MHz		600	-
Instantaneous reverse current	I_R	mA	V_R			

■**Characteristics** (Typical)



■Outline Dimensions & Suggested Pad Layout



Top View

Bottom View

Side View

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.15	6.35
A	1.00	1.10	1.20
A1		0.254 BSC	
A2			0.10
D1	3.92	4.12Q 2	

Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.10mm.
3.The pad layout is for reference purposes only.